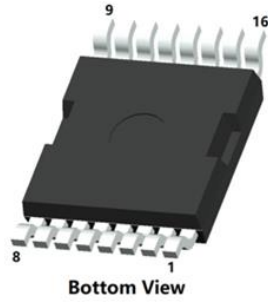
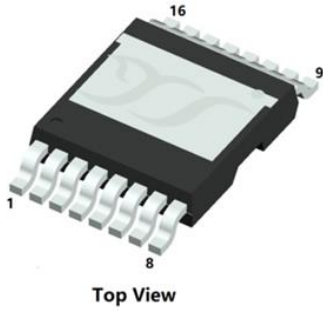
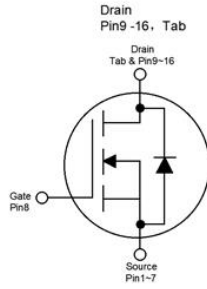


## N-Channel Enhancement Mode Field Effect Transistor



**TOLT**



### Product Summary

- $V_{DS}$  100V
- $I_D$  207A
- $R_{DS(ON)}$  ( at  $V_{GS}=10V$ )  $<2.4m\Omega$
- 100% EAS Tested
- 100%  $\nabla V_{DS}$  Tested

### General Description

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- Load switch
- Battery management
- Solar

### Limiting Values

Parameter	Conditions		Symbol	Min	Max	Unit
Drain-source Voltage			$V_{DS}$	-	100	V
Gate-source Voltage			$V_{GS}$	-20	20	
Continuous Drain Current (Note 1,2)	Steady-State	$T_A=25^\circ C, V_{GS}=10V$	$I_D$	-	27	A
		$T_A=100^\circ C, V_{GS}=10V$		-	19	
Continuous Drain Current (Note 1,3)	Steady-State	$T_C=25^\circ C, V_{GS}=10V, \text{Chip limitation}$		-	207	
		$T_C=100^\circ C, V_{GS}=10V$		-	146	
Pulsed Drain Current	$T_C=25^\circ C, t_p \leq 10\mu s$		$I_{DM}$	-	828	
Maximum Body-Diode Continuous Current	$T_C=25^\circ C$		$I_S$		190	
Avalanche Energy (non-repetitive)	$T_J=25^\circ C, V_G=10V, R_G=25\Omega, L=2mH, I_{AS}=31.5A$		EAS	-	992.2	mJ
Total Power Dissipation (Note 1,2)	Steady-State	$T_A=25^\circ C$	$P_D$	-	3.9	W
		$T_A=100^\circ C$		-	1.9	
Total Power Dissipation (Note 1,3)	Steady-State	$T_C=25^\circ C$		-	223	
		$T_C=100^\circ C$		-	111	
Junction and Storage Temperature Range			$T_J, T_{STG}$	-55	175	$^\circ C$

### Thermal Resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	Steady-State	$R_{\theta JA}$	-	38	$^\circ C/W$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	-	0.67	



# YJTL2D4G10M

## ■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA, T <sub>j</sub> =25°C	100	-	-	V
		V <sub>GS</sub> =0V, I <sub>D</sub> =1mA, T <sub>j</sub> =25°C	100	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V, T <sub>j</sub> =25°C	-	-	1	μA
		V <sub>DS</sub> =100V, V <sub>GS</sub> =0V, T <sub>j</sub> =125°C	-	-	100	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V, T <sub>j</sub> =25°C	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA, T <sub>j</sub> =25°C	2.1	2.9	3.7	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =50A, T <sub>j</sub> =25°C	-	2	2.4	mΩ
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =50A, V <sub>GS</sub> =0V, T <sub>j</sub> =25°C	-	0.83	1.2	V
Gate Resistance	R <sub>G</sub>	f=1MHz, T <sub>j</sub> =25°C	-	2.3	-	Ω
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=0.5MHz, T <sub>j</sub> =25°C	-	7076	-	pF
Output Capacitance	C <sub>oss</sub>		-	2348	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	42	-	
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =50A, T <sub>j</sub> =25°C	-	94	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	30.5	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	15	-	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =50A, di/dt=100A/μs, V <sub>GS</sub> =0V, V <sub>R</sub> =50V, T <sub>j</sub> =25°C	-	50	-	nC
Reverse Recovery Time	t <sub>rr</sub>		-	48	-	ns
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =50A, R <sub>L</sub> =1Ω, R <sub>GEN</sub> =3Ω, T <sub>j</sub> =25°C	-	29	-	ns
Turn-on Rise Time	t <sub>r</sub>		-	54	-	
Turn-off Delay Time	t <sub>D(off)</sub>		-	67	-	
Turn-off Fall Time	t <sub>f</sub>		-	42	-	

### Note:

- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
- The value of R<sub>θJA</sub> is measured with the device mounted on the 40mm\*40mm\*1.1mm single layer FR-4 PCB board with 1 in<sup>2</sup> pad of 2oz. Copper, in the still air environment with T<sub>A</sub>=25°C. The maximum allowed junction temperature of 175°C. The value in any given application depends on the user's specific board design.
- Thermal resistance from junction to soldering point (on the exposed drain pad).



# YJTL2D4G10M

## Typical Electrical and Thermal Characteristics Diagrams

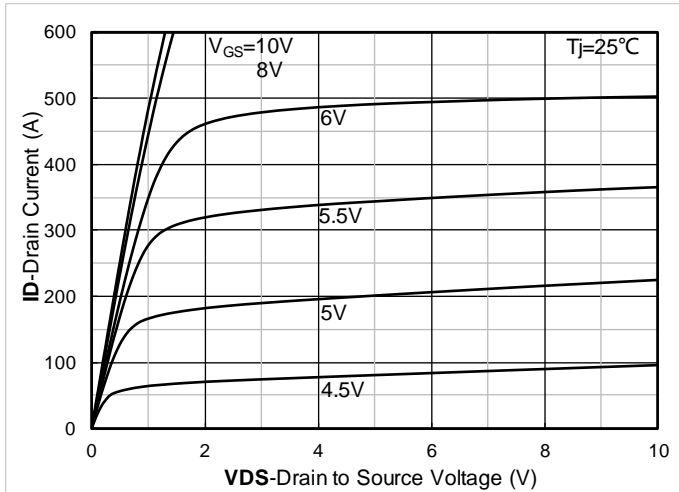


Figure 1. Output Characteristics; typical values

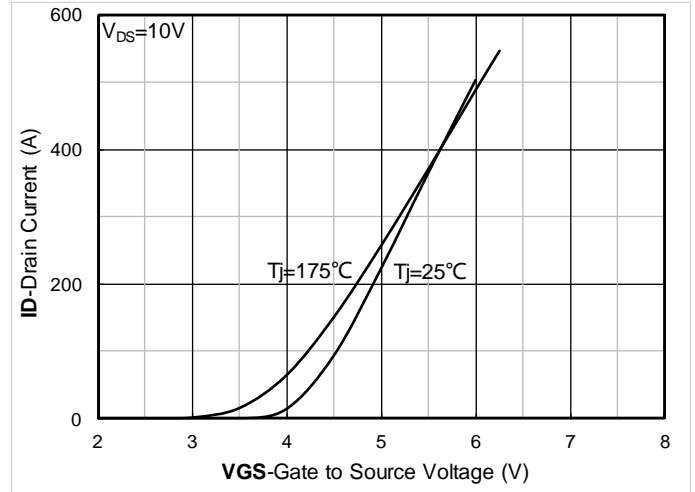


Figure 2. Transfer Characteristics; typical values

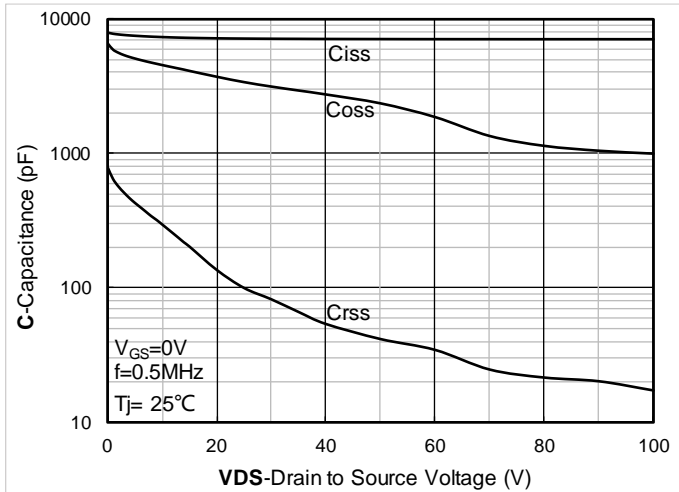


Figure 3. Capacitance Characteristics; typical values

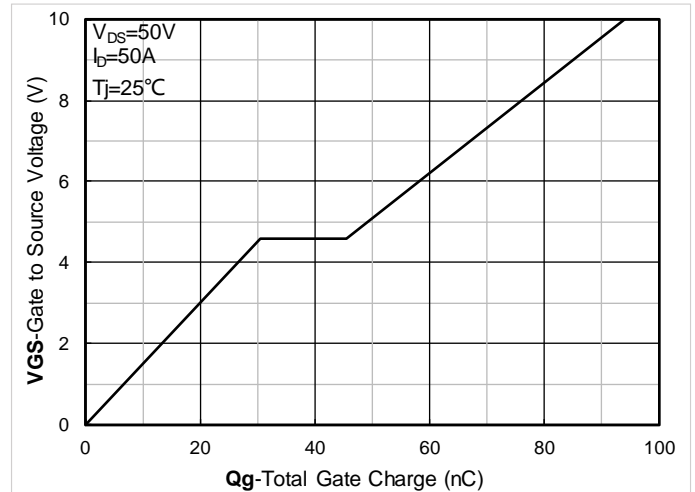


Figure 4. Gate Charge; typical values

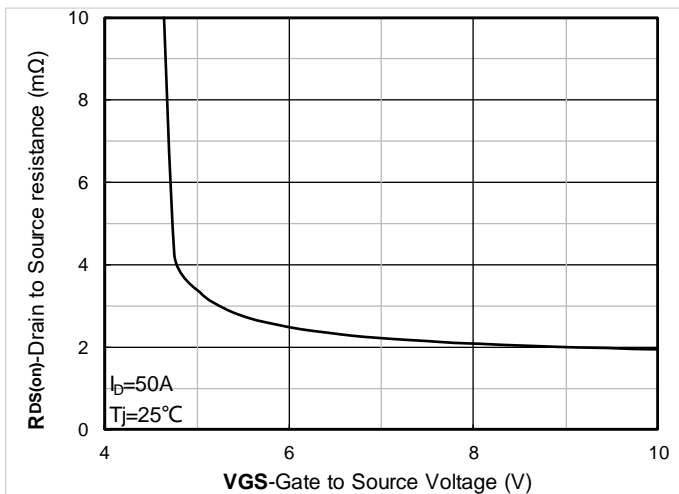


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

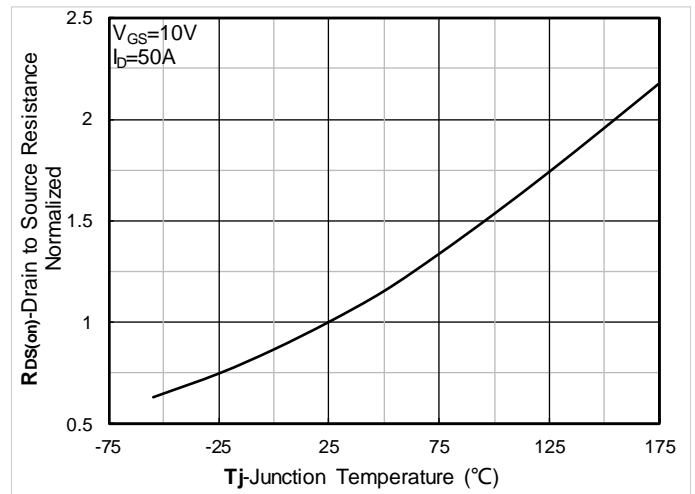


Figure 6. Normalized On-Resistance



# YJTL2D4G10M

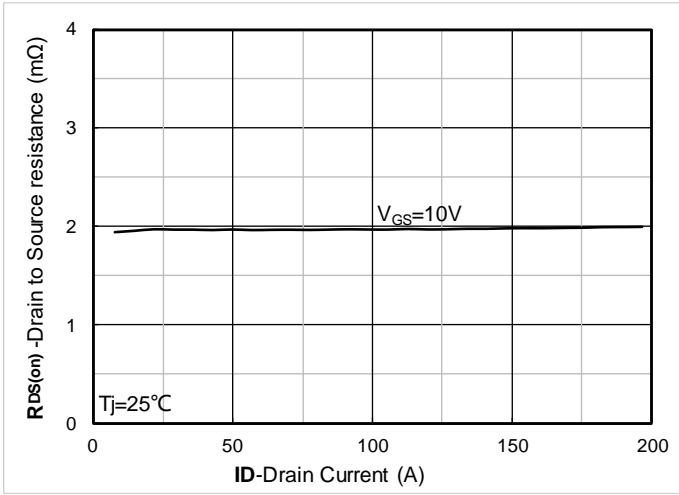


Figure 7. RDS(on) vs. Drain Current; typical values

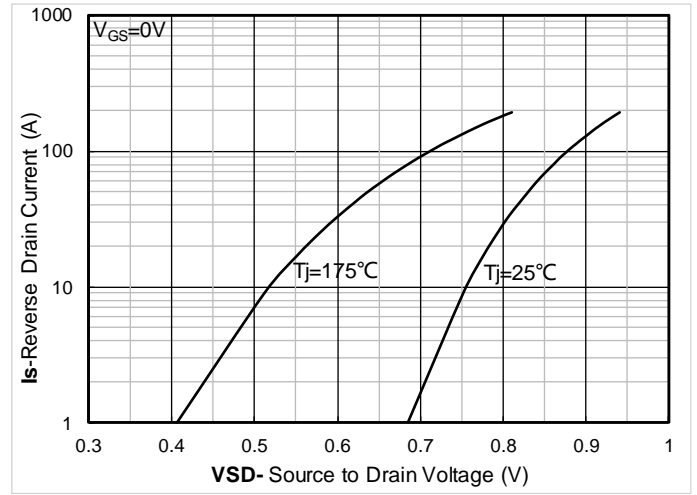


Figure 8. Forward characteristics of reverse diode; typical values

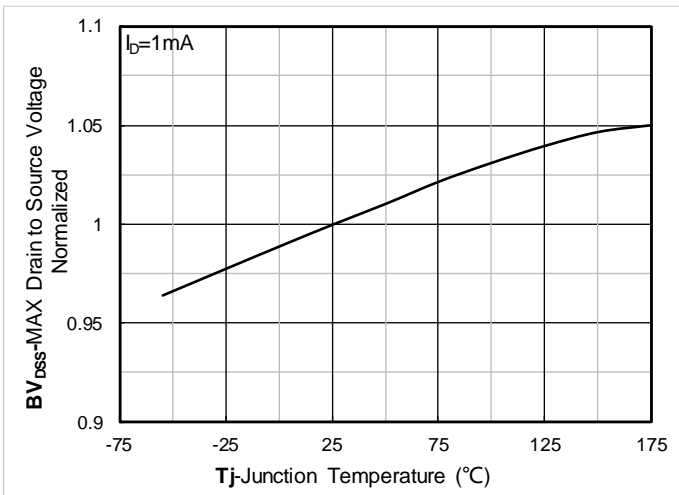


Figure 9. Normalized breakdown voltage

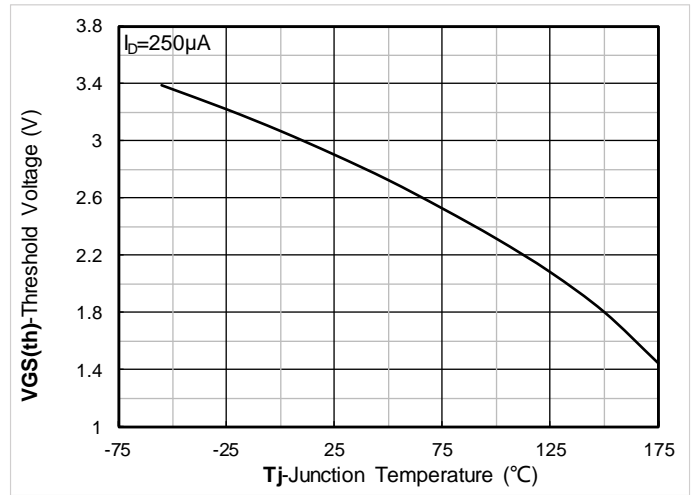


Figure 10. Gate Threshold voltage; typical values

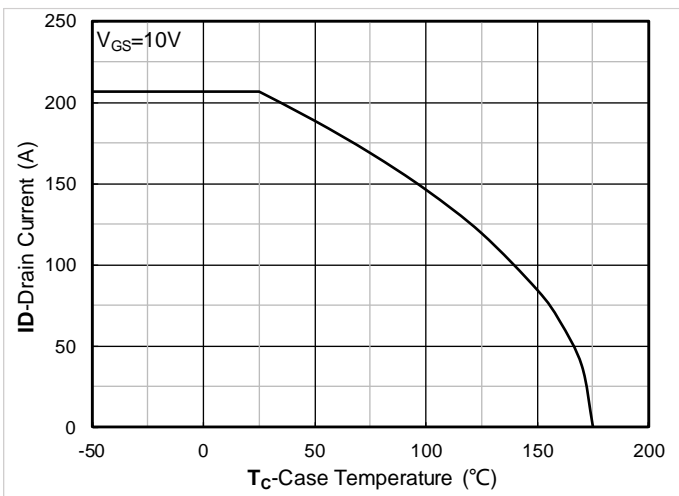


Figure 11. Current dissipation

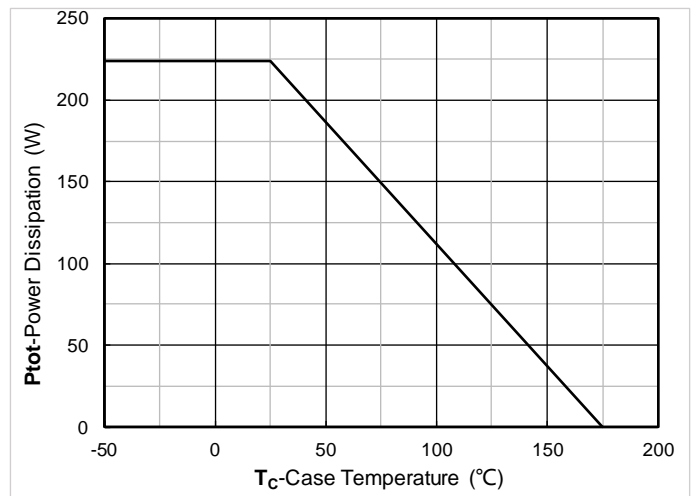


Figure 12. Power dissipation



# YJTL2D4G10M

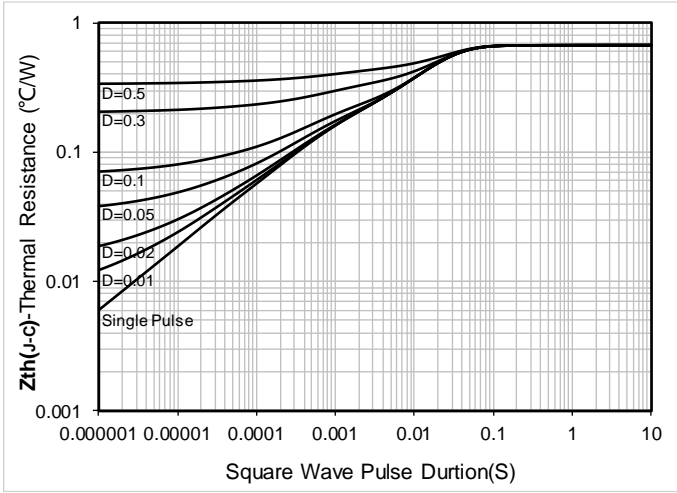


Figure 13. Maximum Transient Thermal Impedance

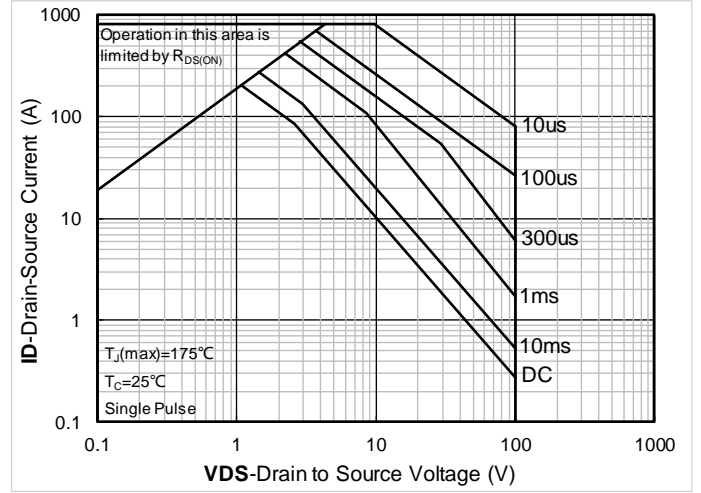


Figure 14. Safe Operation Area

## ■ Test Circuits & Waveforms

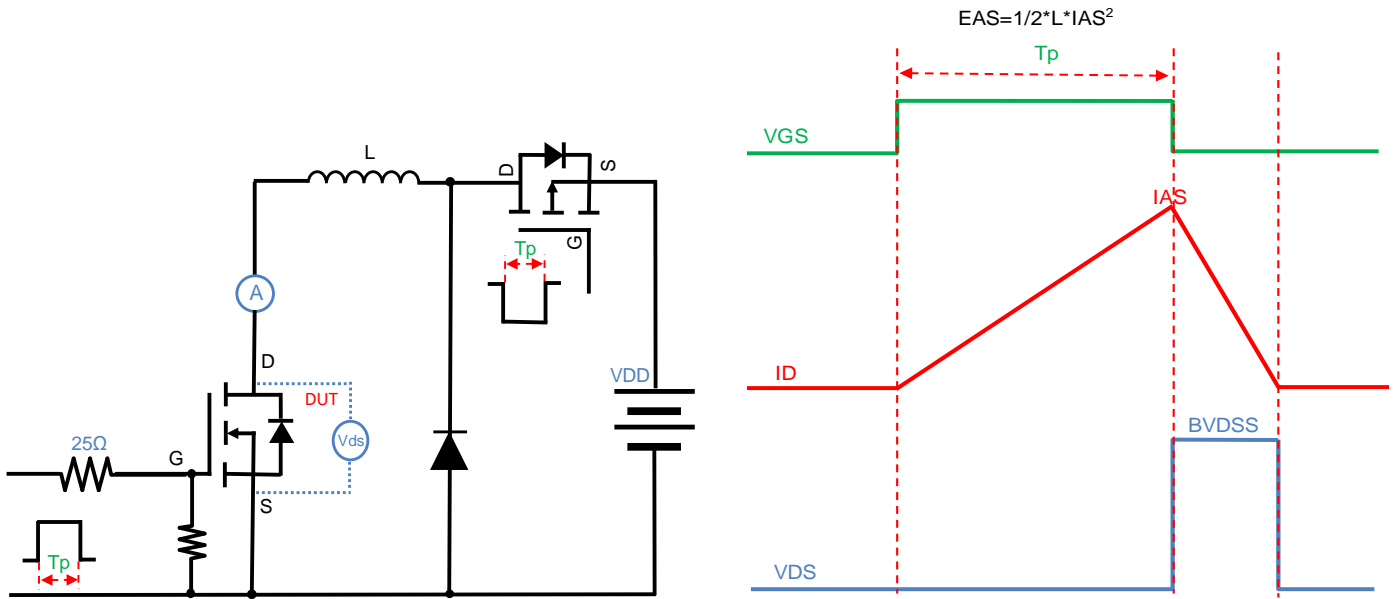


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

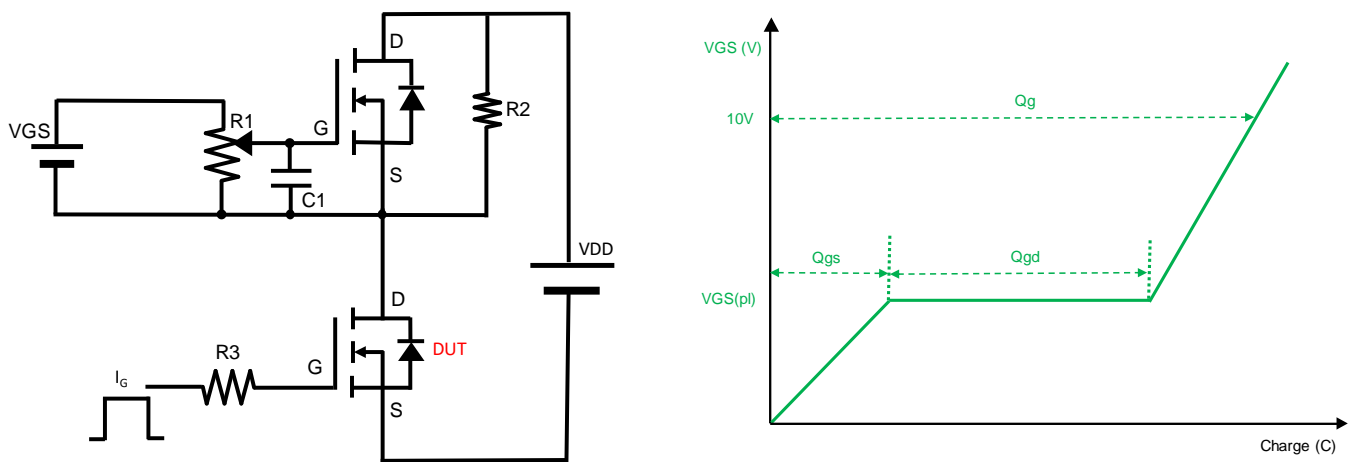


Figure B. Gate Charge Test Circuit & Waveform

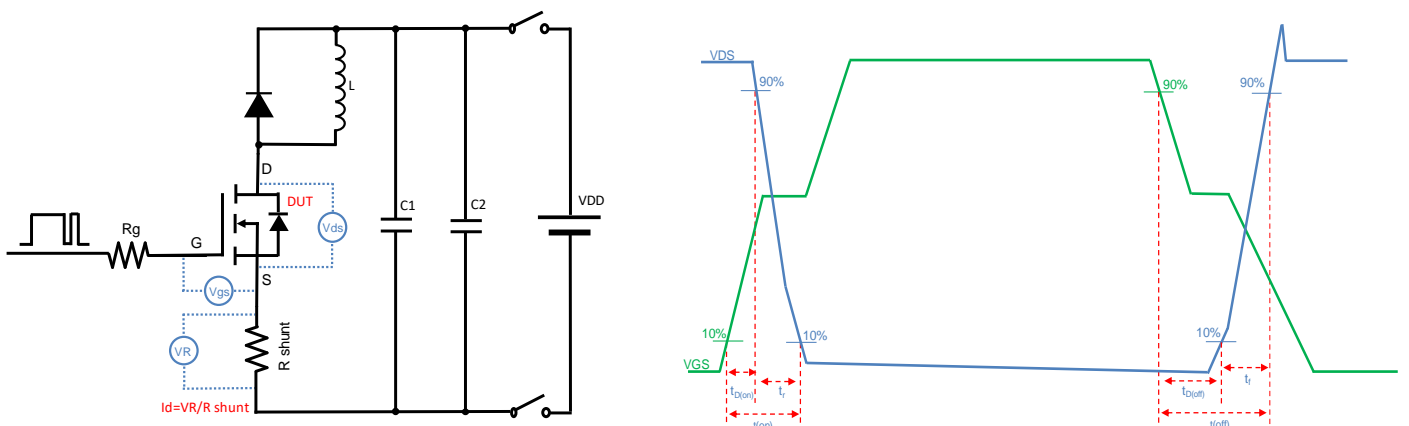


Figure C. Resistive Switching Test Circuit & Waveform

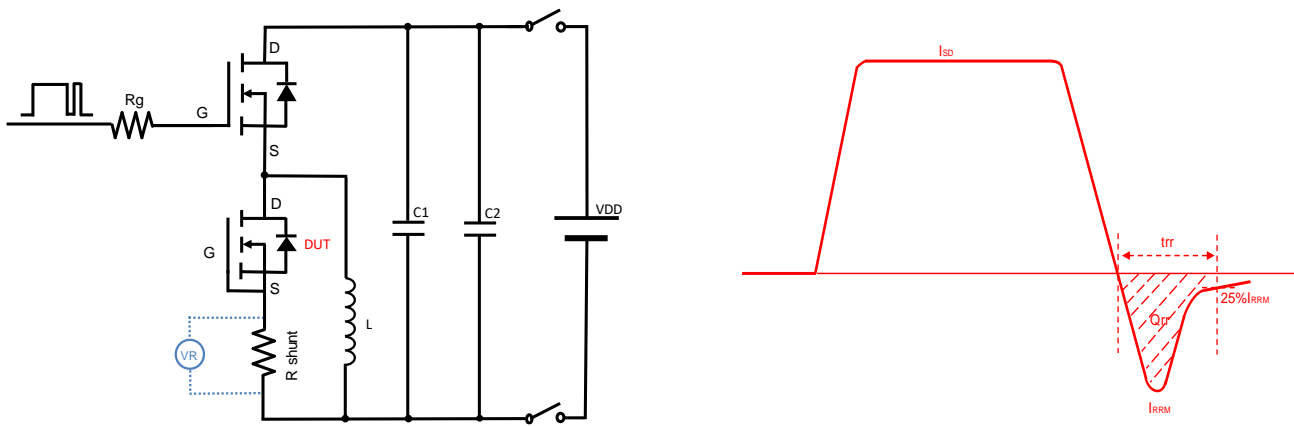
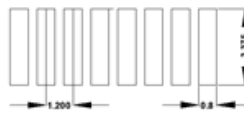
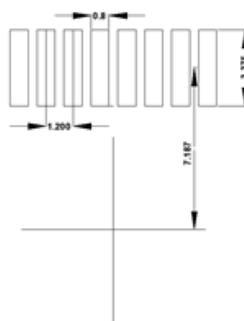
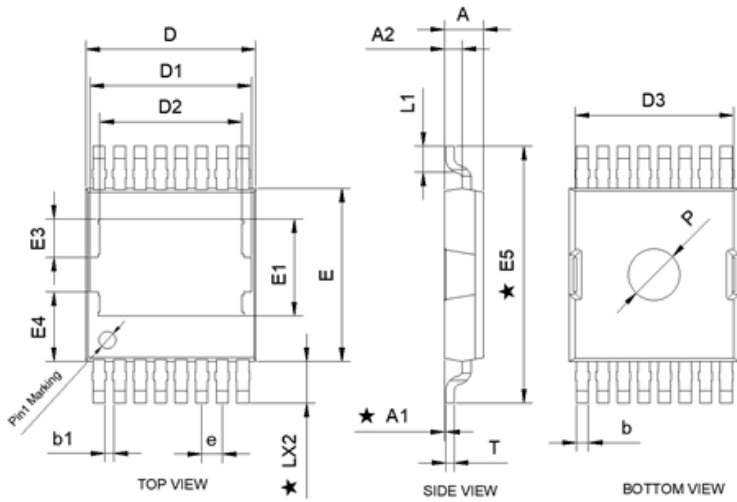


Figure D. Diode Recovery Test Circuit & Waveform



# YJTL2D4G10M

## ■ TOLT Package Information



SUGGESTED SOLDER PAD LAYOUT

SYMBOL	MILLMETER		
	MIN	NOR	MAX
A	2.25	2.30	2.35
A1	0.01	0.08	0.16
A2	0.99	1.04	1.09
b	0.60	0.70	0.80
b1	0.40	0.50	0.60
D	9.70	9.90	10.10
D1	9.36	9.46	9.56
D2	8.20	8.30	8.40
D3	9.17	9.27	9.37
e	1.20BSC		
E	10.00	10.10	10.30
E1	5.47	5.67	5.87
E2	1.90	2.00	2.10
E3	2.05	2.25	2.45
E4	3.90	4.05	4.20
E5	14.80	15.00	15.20
L	2.20	2.45	2.70
L1	1.51REF		
T	0.458	0.508	0.558
P	2.80	3.00	3.20

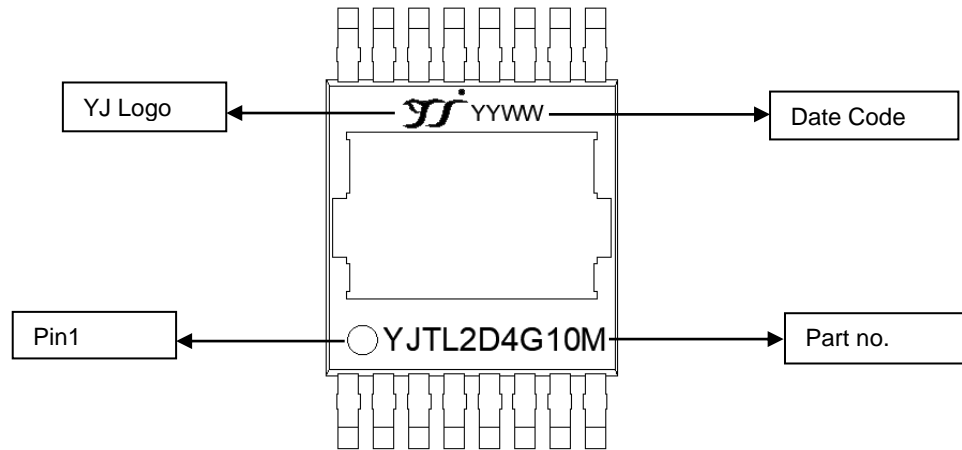
Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.10$ mm.
3. The pad layout is for reference purposes only.
4. ★ It is the key size.



# YJTL2D4G10M

## ■ Marking Information



**Note:**

1. All marking is at middle of the product body
2. All marking is in laser printing
3. YJTL2D4G10M is part no., YYWW is date code, "YY" is year, "WW" is week
4. Body color: Black



# YJTL2D4G10M

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